

RF Low Noise FET CE3512K2

12 GHz Super Low Noise FET in Hollow Plastic PKG

DESCRIPTION

- Super Low Noise and High Gain
- Hollow (Air Cavity) Plastic package

FEATURES

 Super Low noise figure and high associated gain: NF = 0.30 dB TYP., Ga = 13.7 dB TYP.
 @V_{DS} = 2 V, I_D = 10 mA, f = 12 GHz

PACKAGE

Micro-X plastic package



APPLICATIONS

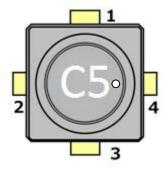
 KU Band LNB (Low Noise Block) Suitable for 1st Stage

ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Description
CE3512K2	CE3512K2-C1	Micro-X plastic package	C5	 Embossed tape 8 mm wide Pin 4 (Gate) faces the perforation side of the tape MOQ 10 kpcs/reel



PIN CONFIGURATION AND INTERNAL BLOCK DIAGRAM



Pin No.	Pin Name
1	Source
2	Drain
3	Source
4	Gate

ABSOLUTE MAXIMUM RATINGS

(TA = +25°C, unless otherwise specified)

Parameter	Symbol	Rating	Unit
Drain to Source Voltage	V_{DS}	4.0	V
Gate to Source Voltage	V_{GS}	-3.0	V
Drain Current	ID	I _{DSS}	mA
Gate Current	I _G	80	μΑ
Total Power Dissipation	P _{tot}	125	mW
Channel Temperature	T _{ch}	+150	°C
Storage Temperature	T _{stg}	-55 to +125	°C
Operation Temperature	T _{op}	-55 to +125 ^{Note}	°C

Note Refer to Total Power Dissipation vs. Ambient Temperature graph on page 4

RECOMMENDED OPERATING RANGE

(TA = +25°C, unless otherwise specified)

(17. 120 6; diffeed otherwise opeomed)					
Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	V _{DS}	+1	+2	+3	V
Drain Current	ΙD	5	10	15	mA



ELECTRICAL CHARACTERISTICS

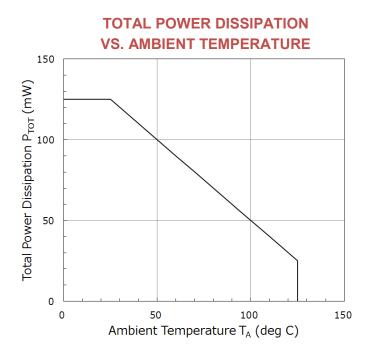
(TA = +25°C, unless otherwise specified)

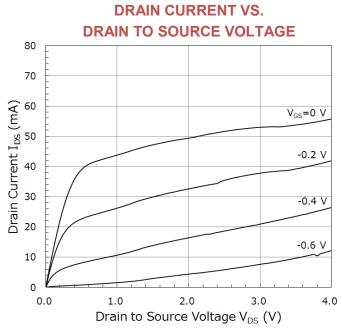
Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Gate to Source Leak Current	I _{GSO}	V _{GS} = -3.0V	-	0.4	10	μΑ
Saturated Drain Current	I _{DSS}	$V_{DS} = 2V$, $V_{GS} = 0V$	27	47.5	68	mA
Gate to Source Cut-off Voltage	$V_{\text{GS(off)}}$	$V_{DS} = 2V$, $I_{D} = 120\mu A$	-1.10	-0.75	-0.39	V
Transconductance	Gm	$V_{DS} = 2V, I_{D} = 10mA$	54	69		mS
Noise Figure	NF	$V_{DS} = 2V, I_{D} = 10mA,$	-	0.30	0.50	dB
Associated Gain	Ga	f = 12GHz	12.5	13.7	-	dB

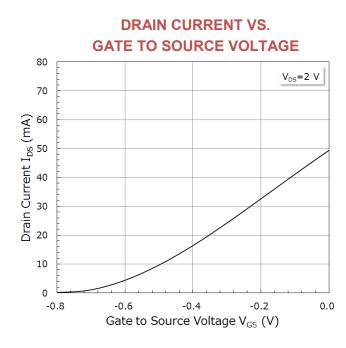


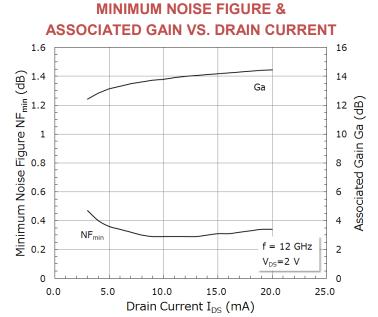
TYPICAL CHARACTERISTICS:

(TA=+25°C, unless otherwise specified)











S-PARAMETERS

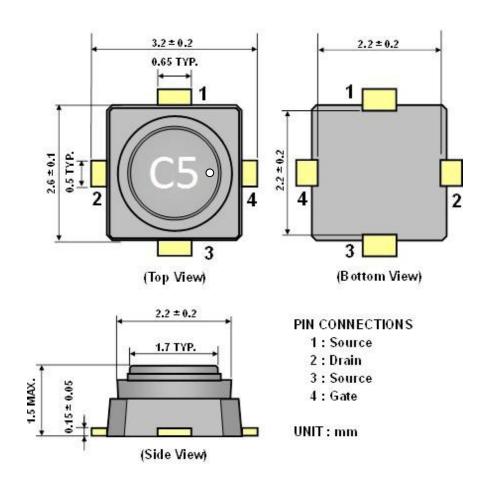
S-Parameters are available on CEL's Part Summary page under S-parameters

RECOMMENDED SOLDERING CONDITIONS

Recommended Soldering Conditions are available on CEL's Part Summary page under Associated Documents

PACKAGE DIMENSIONS

Micro-X plastic package





REVISION HISTORY

Version	Change to current version	Page(s)
CDS-0018-04 (Issue A) February 12, 2016	Initial datasheet	N/A
CDS-0018-04 (Issue B) April 27, 2016	Updated Marking Information	1, 2, 3
CDS-0018-05 (Issue A) July 29, 2016	Updated Specs in "Absolute Maximum Ratings" Table Added "Typical Characteristics" section (graphs) Added "S-Parameters" and "Recommended Soldering Conditions" sections	2, 4, 5
CDS-0018-05 (Issue B) Nov 29, 2018	Updated Applications Updated marking by adding a dot to the package Gate	1, 2, 5



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[CAUTION]

This product uses gallium arsenide (GaAs) of the toxic substance appointed in laws and ordinances. GaAs vapor and powder are hazardous to human health if inhaled or ingested.

- Do not dispose in fire or break up this product.
- Do not chemically make gas or powder with this product.
- When discarding this product, please obey the laws of your country.
- Do not lick the product or in any way allow it to enter the mouth.

[CAUTION]

Although this device is designed to be as robust as possible, ESD (Electrostatic Discharge) can damage this device. This device must be protected at all times from ESD. Static charges may easily produce potentials of several kilovolts on the human body or equipment, which can discharge without detection. Industry-standard ESD precautions should be used at all times.

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